=> file reg FILE 'REGISTRY' ENTERED AT 14:05:25 ON 28 JUL 2005 USE IS SUBJECT TO THE TERMS OF YOUR STN CUSTOMER AGREEMENT. PLEASE SEE "HELP USAGETERMS" FOR DETAILS. COPYRIGHT (C) 2005 American Chemical Society (ACS)

=> d his

FILE 'LREGISTRY' ENTERED AT 13:36:36 ON 28 JUL 2005 L1 STR

FILE 'REGISTRY' ENTERED AT 13:47:01 ON 28 JUL 2005

L2 SCR 2043

L3 0 S L1 AND L2

L4 0 S L1 AND L2 FUL

FILE 'HCAPLUS' ENTERED AT 14:03:22 ON 28 JUL 2005

L5 238 S YUEH ?/AU

L6 32 S PUTNA ?/AU

L7 1 S L5 AND L6

FILE 'REGISTRY' ENTERED AT 14:05:25 ON 28 JUL 2005

=> d 14 que stat

L1 STR

$$\begin{array}{c}
c = c^{2} \\
1 \\
3 \\
C = 0 \\
7 \\
0 \\
4 \\
9 \\
Ak \nearrow C \\
G \\
6
\end{array}$$
14 S E1

REP G1=(1-5) C
NODE ATTRIBUTES:
HCOUNT IS E1 AT 14
CONNECT IS E1 RC AT 9
CONNECT IS X1 RC AT 14
DEFAULT MLEVEL IS ATOM

GGCAT IS SAT AT 9
DEFAULT ECLEVEL IS LIMITED

GRAPH ATTRIBUTES:

RING(S) ARE ISOLATED OR EMBEDDED NUMBER OF NODES IS 10

STEREO ATTRIBUTES: NONE L2 SCR 2043

L4 0 SEA FILE=REGISTRY SSS FUL L1 AND L2

100.0% PROCESSED 1347 ITERATIONS

SEARCH TIME: 00.00.01

0 ANSWERS

=> file hcaplus FILE 'HCAPLUS' ENTERED AT 14:05:34 ON 28 JUL 2005 USE IS SUBJECT TO THE TERMS OF YOUR STN CUSTOMER AGREEMENT. PLEASE SEE "HELP USAGETERMS" FOR DETAILS. COPYRIGHT (C) 2005 AMERICAN CHEMICAL SOCIETY (ACS)

## => d 17 1 all

authors ortation

L7 ANSWER 1 OF 1 HCAPLUS COPYRIGHT 2005 ACS on STN

AN 2005:638587 HCAPLUS

ED Entered STN: 22 Jul 2005

TI Reducing outgassing of reactive material upon exposure of photolithography resists

IN Yueh, Wang; Putna, Ernisse S.

PA USA

SO U.S. Pat. Appl. Publ., 4 pp.

CODEN: USXXCO

DT Patent

LA English

IC ICM G03C001-492

INCL 430270100

CC 74 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

FAN.CNT 1

LTMV.	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2005158654	A1	20050721	US 2004-761842	200401

LEE 10/815,398

PRAI US 2004-761842

20040121

CLASS

PATENT NO.	CLASS	PATENT FAMILY CLASSIFICATION CODES
US 20050158654		G03C001-492
•	INCL	430270100
US 2005158654	NCL	430/270.100

AB Outgassing of reactive material upon exposure of a photolithographic resist may be reduced. Outgassing may foul optical components of the photolithographic system. In one embodiment, a ring compound with iodine or sulfur may be formed. The ring compound may be more resistant to the generation of reactive outgassing components.